

1-6-4

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

**Title of
Invention****STRUCTURE AND METHOD OF MAKING HETEROJUNCTION
BIPOLAR TRANSISTOR HAVING SELF-ALIGNED
SILICON-GERMANIUM RAISED EXTRINSIC BASE**

Application Number : 10/707712

Confirmation Number:

First Named Applicant: Kevin Chan






Attorney Docket Number: FIS920030310US1

Art Unit: 2815

Examiner: Jackson

Search string: (5128271 or 5494836 or 5506427 or 5962880 or 6346453).pn

US Patent Documents**Note: Applicant is not required to submit a paper copy of cited US Patent Documents**

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5128271	1992-07-07	Bronner, et al.			
	2	5494836	1996-02-27	Imai			
	3	5506427	1996-04-09	Imai			
	4	5962880	1999-10-05	Oda, et al.			
	5	6346453	2002-02-12	Kovacic, et al.			

Signature

Examiner Name	Date
	2/05